

SN65LVDTxx マルチ・チャネル LVDS トランシーバ

SN65LVDT14 - 1つの LVDS ドライバと 4 つの LVDS レシーバ

SN65LVDT41 - 4 つの LVDS ドライバと 1 つの LVDS レシーバ

1 特長

- 公称 110Ω のレシーバ・ライン終端抵抗を内蔵
- 3.3V 単一電源 (3V~3.6V の範囲)
- 最低 250Mbps の信号速度をサポート
- フロッスルーのピン配置により PCB レイアウトを簡素化
- LVTTL 互換のロジック I/O
- バス・ピンで 16kV を超える ESD 保護
- ANSI/TIA/EIA-644A 規格の LVDS の要件を満たすか、上回る性能
- 20 ピンの PW シン・シュリンク・スモール・アウトライン・パッケージ (TSSOP)、端子ピッチ 26mil

2 アプリケーション

- Serial Peripheral Interface™(SPI) over LVDS による、マスタとスレーブの間の長い相互接続が可能
- 基板間通信
- 試験/測定
- モータ・ドライブ
- LEDビデオ・ウォール
- ワイヤレス・インフラ
- 通信インフラ
- ラック・サーバー

3 概要

SN65LVDTxx デバイスは、LVDS ライン・ドライバおよびレシーバを使用して動作するマルチチャネル LVDS トランシーバです。SN65LVDTxx デバイスは 250Mbps 以上の信号速度をサポートしています。単一電源 (標準 3.3V) で動作し、20 ピン TSSOP パッケージを使用して PCB レイアウトが簡単に行えるよう設計されています。

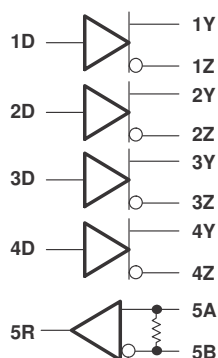
SN65LVDT14 と SN65LVDT41 は汎用の非対称、双方向通信を提供します。さらに、LVDS ラインを使用することで高いノイズ耐性、低い電磁妨害 (EMI)、長いケーブル長という利点も備えています。SN65LVDT14 と SN65LVDT41 は主に、SPI over LVDS アプリケーションで使用されます。

製品情報⁽¹⁾

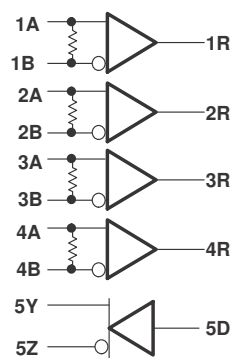
型番	パッケージ	本体サイズ(公称)
SN65LVDT14 SN65LVDT41	TSSOP (20)	6.50mm×4.40mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

SN65LVDT41 の機能図



SN65LVDT14 の機能図



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4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision B (February 2006) から Revision C に変更

Page

- 「製品情報」表、「ESD 定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加 **1**
- データシートのページの上端にナビゲーション・リンクを追加し、NRND バナーを削除 **1**
- Moved power dissipation parameter to the *Absolute Maximum Ratings* table..... **6**

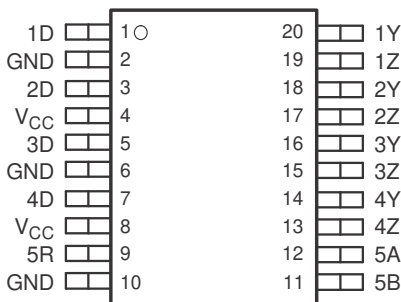
5 概要（続き）

SN65LVDT14 は、1 つの LVDS ライン・ドライバと、4 つの終端付き LVDS ライン・レシーバを、1 つのパッケージに統合したものです。SN65LVDT14 は、非対称の双方向インターフェイスを拡張するため (長距離の SPI など) に使用でき、SPI スレーブの近くに配置する必要があります。

SN65LVDT41 は、4 つの LVDS ライン・ドライバと、1 つの終端付き LVDS ライン・レシーバを、1 つのパッケージに統合したものです。SN65LVDT41 は、非対称の双方向インターフェイスを拡張するため (長距離の SPI など) に使用でき、SPI マスタの近くに配置する必要があります。

6 Pin Configuration and Functions

**SN65LVDT41 PW Package
20-Pin TSSOP
Top View**



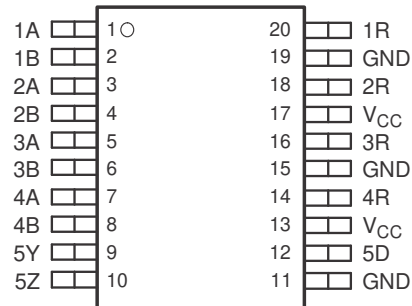
*marked as LVDT41

SN65LVDT41 Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1D ⁽¹⁾	1	I	LVTTTL Driver Input Pin
2D ⁽¹⁾	3		
3D ⁽¹⁾	5		
4D ⁽¹⁾	7		
1Y ⁽¹⁾	20	O	Noninverting LVDS Driver Output Pin
2Y ⁽¹⁾	18		
3Y ⁽¹⁾	16		
4Y ⁽¹⁾	14		
1Z ⁽¹⁾	19	O	Inverting LVDS Driver Output Pin
2Z ⁽¹⁾	17		
3Z ⁽¹⁾	15		
4Z ⁽¹⁾	13		
5R	9	O	LVTTTL Receiver Output Pin
5A	12	I	Noninverting LVDS Receiver Input Pin
5B	11	I	Inverting LVDS Receiver Input Pin
V _{CC}	4, 8	I	Power Supply Pin, +3.3 V ± 0.3 V
GND	2, 6, 10	I	Ground Pin

(1) x = 1, 2, 3, 4 indicating channel number of SN65LVDT41

**SN65LVDT14 PW Package
20-Pin TSSOP
Top View**



*marked as LVDT14

SN65LVDT14 Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1A ⁽¹⁾	1	I	Noninverting LVDS Receiver Input Pin
2A ⁽¹⁾	3		
3A ⁽¹⁾	5		
4A ⁽¹⁾	7		
1B ⁽¹⁾	2	I	Inverting LVDS Receiver Input Pin
2B ⁽¹⁾	4		
3B ⁽¹⁾	6		
4B ⁽¹⁾	8		
1R ⁽¹⁾	20	O	LVTTTL Receiver Output Pin
2R ⁽¹⁾	18		
3R ⁽¹⁾	16		
4R ⁽¹⁾	14		
5Y	9	I	Noninverting LVDS Driver Output Pin
5Z	10	I	Inverting LVDS Driver Output Pin
5D	12	O	LVTTTL Driver Input Pin
GND	11, 15, 19	I	Ground Pin
V _{CC}	13, 17	I	Power Supply Pin, +3.3 V ± 0.3 V

(1) x = 1, 2, 3, 4 indicating channel number of SN65LVDT41

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted⁽¹⁾

		MIN	MAX	UNIT
Supply voltage ⁽²⁾	V _{CC}	–0.5	4	V
Input voltage	D or R	–0.5	6	V
	A, B, Y, or Z	–0.5	4	V
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds			260	°C
Continuous total power dissipation	T _A < 25°C power rating		774	mW
	T _A = 85°C power rating		402	
	Operating factor above T _A = 25°C		6.2	mW/°C
Storage temperature, T _{stg}		–65	150	°C

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential I/O bus voltages are with respect to network ground terminal.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD) Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	All pins except A, B, Y, Z, and GND ⁽²⁾	±8000	V
		Pins A, B, Y, Z, and GND ⁽³⁾	±16000	
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽⁴⁾⁽⁵⁾		±500	

- (1) Tested in accordance with JEDEC Standard 22, Test Method A114-A.
- (2) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Pins listed as ±8000 V may actually have higher performance.
- (3) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Pins listed as ±16000 V may actually have higher performance.
- (4) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Pins listed as ±500 V may actually have higher performance.
- (5) Tested in accordance with JEDEC Standard 22, Test Method C101.

7.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	3	3.3	3.6	V
V _{IH}	High-level input voltage	2			V
V _{IL}	Low-level input voltage			0.8	V
V _{ID}	Magnitude of differential input voltage	0.1		0.6	V
V _{IC}	Common-mode input voltage, See Figure 1	$\frac{ V_{ID} }{2}$	2.4	$-\frac{ V_{ID} }{2}$	V
			V _{CC} – 0.8		V
T _A	Operating free-air temperature	–40		85	°C

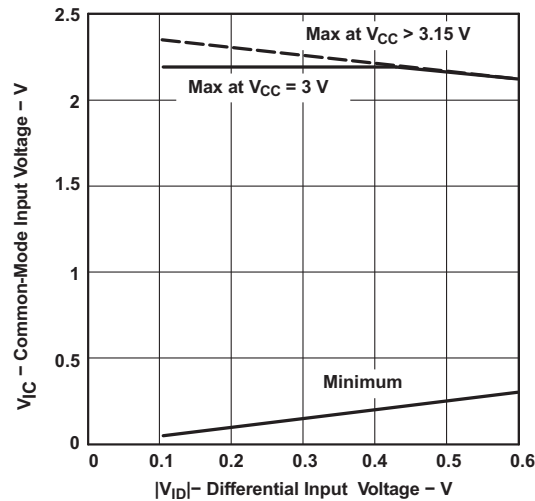


Figure 1. V_{IC} vs V_{ID} and V_{CC}

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN65LVDTxx	UNIT	
		PW (TSSOP)		
		20 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86.9	°C/W	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	28.4	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	38.2	°C/W	
ψ_{JT}	Junction-to-top characterization parameter	1.4	°C/W	
ψ_{JB}	Junction-to-board characterization parameter	37.8	°C/W	

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report (SPRA953).

7.5 Receiver Electrical Characteristics

over operating free-air temperature range unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{ITH+}	Positive-going differential input voltage threshold	See Figure 8 and Table 1		100	mV
V_{ITH-}	Negative-going differential input voltage threshold			-100	
V_{OH}	High-level output voltage	$I_{OH} = -8$ mA		2.4	V
V_{OL}	Low-level output voltage	$I_{OL} = 8$ mA		0.4	V
I_I	Input current (A or B inputs)	$V_I = 0$ V and $V_I = 2.4$ V, other input open		±40	µA
$I_{I(OFF)}$	Power-off input current (A or B inputs)	$V_{CC} = 0$ V, $V_I = 2.4$ V		±40	µA
C_i	Input capacitance, A or B input to GND	$V_I = A \sin 2\pi f t + CV$		5	pF
Z_t	Termination impedance	$V_{ID} = 0.4 \sin 2.5E09 t$ V		88	Ω

(1) All typical values are at 25°C and with a 3.3-V supply.

7.6 Driver Electrical Characteristics

over operating free-air temperature range unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
$ V_{OD} $	Differential output voltage magnitude	$R_L = 100\ \Omega$, See Figure 9 and Figure 12	247	340	454	mV
$\Delta V_{OD} $	Change in differential output voltage magnitude between logic states		–50		50	
$V_{OC(SS)}$	Steady-state common-mode output voltage	See Figure 13	1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage between logic states		–50		50	mV
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage			50	150	mV
I_{IH}	High-level input current	$V_{IH} = 2\ V$			20	μA
I_{IL}	Low-level input current	$V_{IL} = 0.8\ V$			10	μA
I_{OS}	Short-circuit output current	V_{OY} or $V_{OZ} = 0\ V$			± 24	mA
		$V_{OD} = 0\ V$			± 12	
$I_{O(OFF)}$	Power-off output current	$V_{CC} = 1.5\ V$, $V_O = 2.4\ V$			± 1	μA

(1) All typical values are at 25°C and with a 3.3-V supply.

7.7 Device Electrical Characteristics

over operating free-air temperature range unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC}	Supply current	SN65LVDT14	Driver $R_L = 100\ \Omega$, Driver $V_I = 0.8\ V$ or $2\ V$, Receiver $V_I = \pm 0.4\ V$		25	mA
		SN65LVDT41			35	

(1) All typical values are at 25°C and with a 3.3-V supply.

7.8 Receiver Switching Characteristics

over operating free-air temperature range unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	NOM	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	$C_L = 10\ pF$, See Figure 11	1	2.6	3.8	ns
t_{PHL}	Propagation delay time, high-to-low-level output		1	2.6	3.8	ns
t_r	Output signal rise time		0.15		1.2	ns
t_f	Output signal fall time		0.15		1.2	ns
$t_{sk(p)}$	Pulse skew ($ t_{PHL} - t_{PLH} $)			150	600	ps
$t_{sk(o)}$	Output skew ⁽¹⁾			100	400	ps
$t_{sk(pp)}$	Part-to-part skew ⁽²⁾				1	ns

(1) $t_{sk(o)}$ is the magnitude of the time difference between the t_{PLH} or t_{PHL} of all the receivers of a single device with all of their inputs connected together.

(2) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

7.9 Driver Switching Characteristics

over operating free-air temperature range unless otherwise noted

PARAMETER		TEST CONDITIONS	MIN	NOM	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	$R_L = 100\ \Omega$, $C_L = 10\ pF$, See Figure 14	0.9	1.7	2.9	ns
t_{PHL}	Propagation delay time, high-to-low-level output		0.9	1.6	2.9	
t_r	Differential output signal rise time		0.26		1	
t_f	Differential output signal fall time		0.26		1	

Driver Switching Characteristics (continued)

over operating free-air temperature range unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	NOM	MAX	UNIT
$t_{sk(p)}$ Pulse skew ($ t_{pHL} - t_{pLH} $)	$R_L = 100 \Omega$, $C_L = 10 \text{ pF}$, See Figure 14		150	500	ps
$t_{sk(o)}$ Output skew ⁽¹⁾			80	150	ps
$t_{sk(pp)}$ Part-to-part skew ⁽²⁾				1.5	ns

(1) $t_{sk(p)}$ is the magnitude of the time difference between the high-to-low and low-to-high propagation delay times at an output.

(2) $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

7.10 Typical Characteristics

7.10.1 Receiver

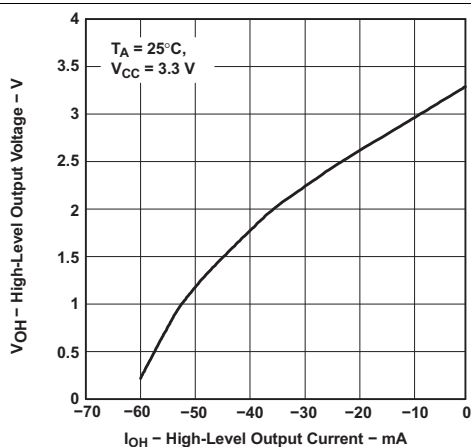


Figure 2. High-Level Output Voltage vs High-Level Output Current

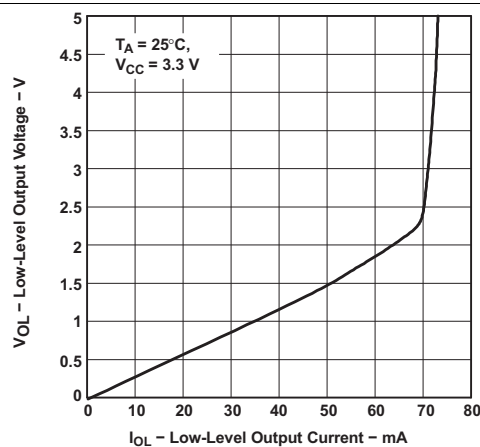


Figure 3. Low-Level Output Voltage vs Low-Level Output Current

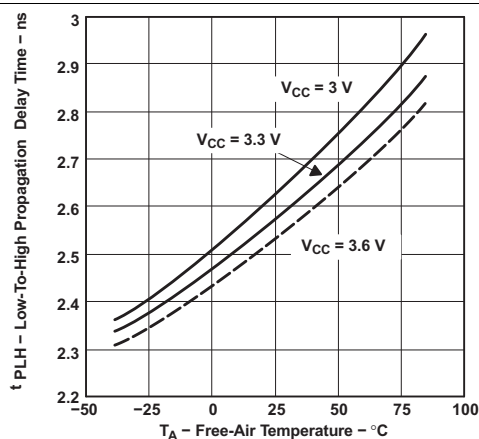


Figure 4. Low-to-High Propagation Delay Time vs Free-Air Temperature

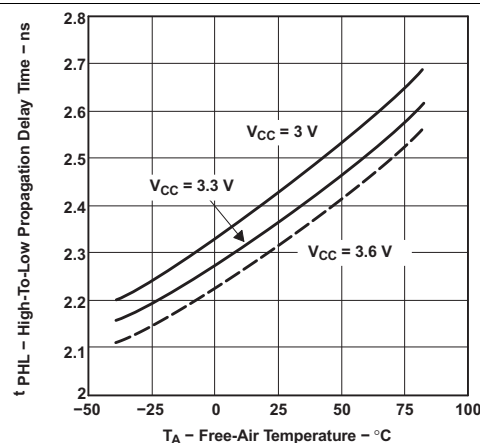


Figure 5. High-to-Low Propagation Delay Time vs Free-Air Temperature

7.10.2 Driver

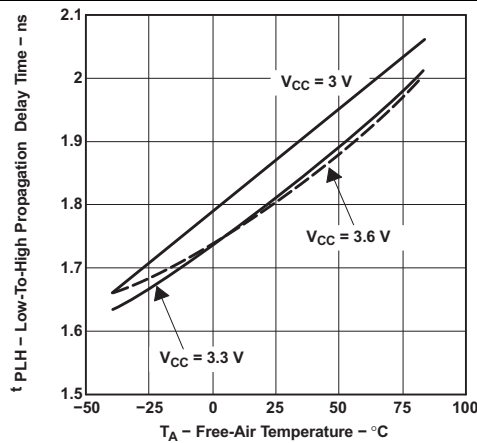


Figure 6. Low-to-High Propagation Delay Time vs Free-Air Temperature

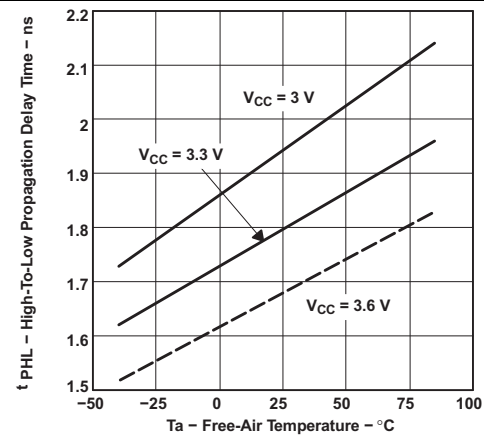


Figure 7. High-to-Low Propagation Delay Time vs Free-Air Temperature

8 Parameter Measurement Information

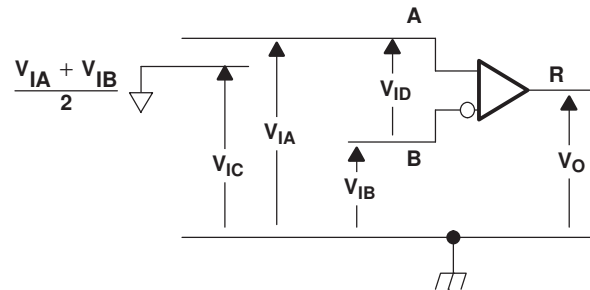


Figure 8. Receiver Voltage Definitions

Table 1. Receiver Minimum and Maximum Input Threshold Test Voltages

APPLIED VOLTAGES		RESULTING DIFFERENTIAL INPUT VOLTAGE	RESULTING COMMON-MODE INPUT VOLTAGE
V_{IA}	V_{IB}	V_{ID}	V_{IC}
1.25 V	1.15 V	100 mV	1.2 V
1.15 V	1.25 V	-100 mV	1.2 V
2.4 V	2.3 V	100 mV	2.35 V
2.3 V	2.4 V	-100 mV	2.35 V
0.1 V	0.0 V	100 mV	0.05 V
0.0 V	0.1 V	-100 mV	0.05 V
1.5 V	0.9 V	600 mV	1.2 V
0.9 V	1.5 V	-600 mV	1.2 V
2.4 V	1.8 V	600 mV	2.1 V
1.8 V	2.4 V	-600 mV	2.1 V
0.6 V	0.0 V	600 mV	0.3 V
0.0 V	0.6 V	-600 mV	0.3 V

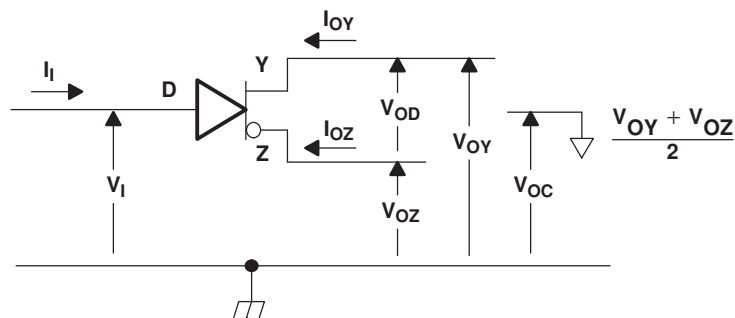


Figure 9. Driver Voltage and Current Definitions

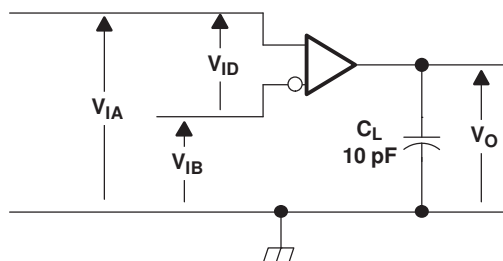
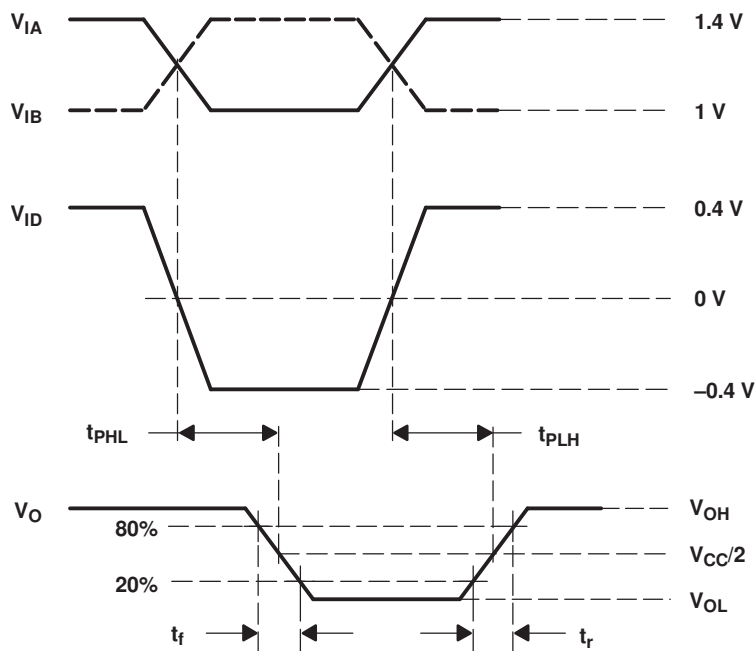
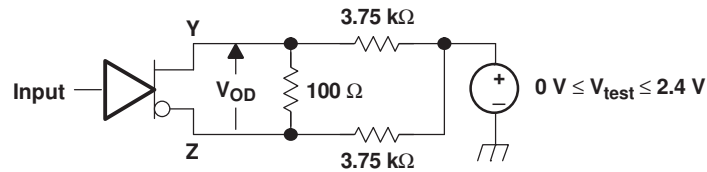
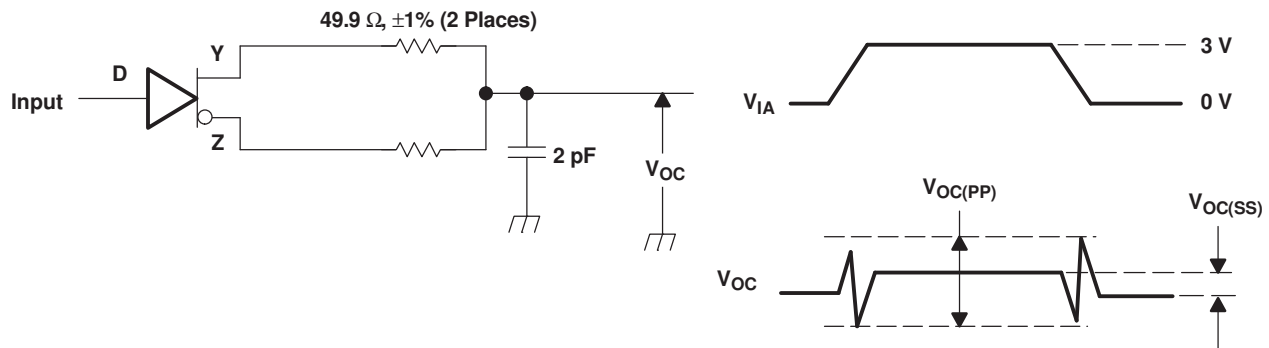


Figure 10. Receiver Timing Test Circuit

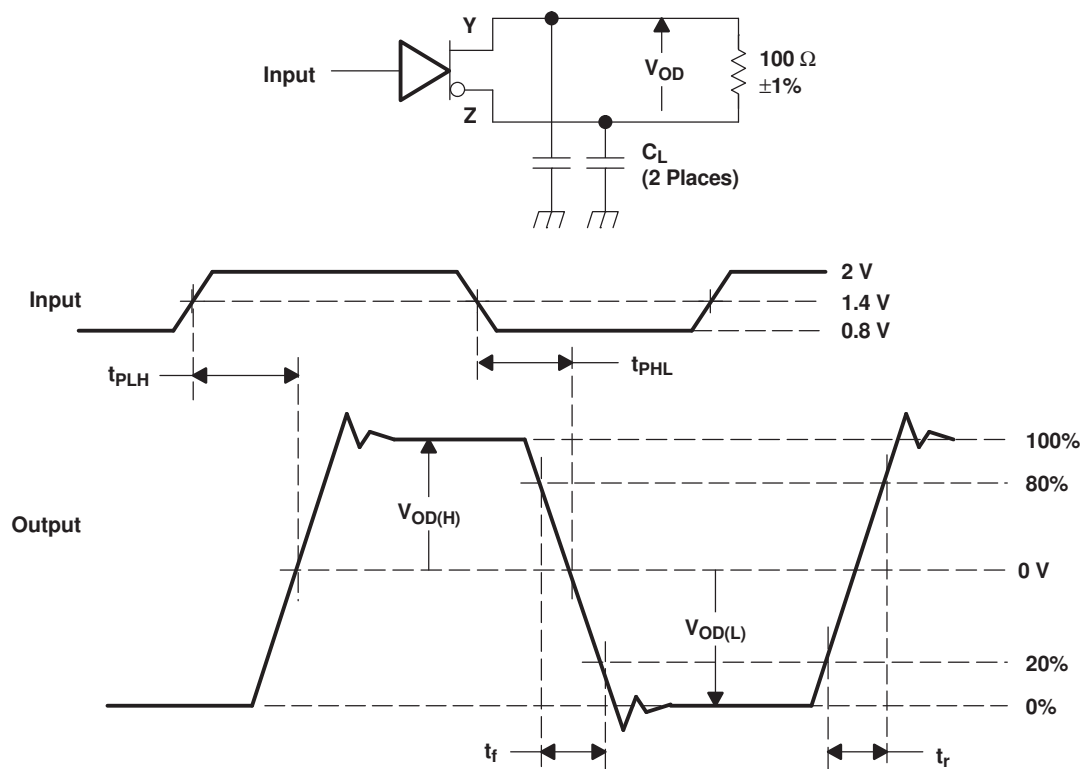


- A. All input pulses are supplied by a generator having the following characteristics: t_f or $t_r \leq 1$ ns, pulse repetition rate (PRR) = 1 Mpps, pulse width = 0.5 ± 0.05 μ s. C_L includes instrumentation and fixture capacitance within 0,06 m of the D.U.T.

Figure 11. Receiver Timing Test Circuit Waveforms


Figure 12. Driver VDO Test Circuit


- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, pulse repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ± 10 ns. C_L includes instrumentation and fixture capacitance within 0.06 mm of the D.U.T. The measurement of $V_{OC(PP)}$ is made on test equipment with a –3-dB bandwidth of at least 1 GHz.

Figure 13. Test Circuit and Definitions for the Driver Common-Mode Output Voltage


- A. All input pulses are supplied by a generator having the following characteristics: t_r or $t_f \leq 1$ ns, pulse repetition rate (PRR) = 1 Mpps, pulse width = 0.5 ± 0.05 μ s. C_L includes instrumentation and fixture capacitance within 0.06 mm of the D.U.T.

Figure 14. Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal

9 Detailed Description

9.1 Overview

The SN65LVDTxx integrates both low-voltage differential signaling (LVDS) line drivers, with a balanced current source design, and LVDS line receivers into a single package. This device operates from a single supply that is nominally 3.3 V, but the supply can be as low as 3 V and as high as 3.6 V. The input to the SN65LVDTxx LVDS drivers is a LVC MOS/LVTTL signal, and the output is a differential signal complying with the LVDS standard (TIA/EIA-644). The input to the SN65LVDTxx LVDS receivers is a differential signal complying with the LVDS Standard (TIA/EIA-644), and the output is a 3.3-V LVC MOS/LVTTL signal. The differential output signal of the SN65LVDTxx LVDS line drivers operates with a signal level of 350 mV, nominally, at a common-mode voltage of 1.2 V. This low differential output voltage results in low electromagnetic interference (EMI). The differential input signal of the SN65LVDTxx LVDS line receivers operates with a signal level of 350 mV, nominally, at a common-mode voltage of 1.2 V. The differential nature of the LVDS outputs and inputs can provide immunity to common-mode coupled signals (noise) that the driven/received signal may experience, along with a low EMI solution.

The SN65LVDTxx can be used to extend asymmetric bidirectional interface buses. The SN65LVDT41 combines four LVDS line drivers with a single terminated LVDS line receiver in one package, and the SN65LVDT14 combines one LVDS line driver with four terminated LVDS line receivers in one package. The SN65LVDTxx can be used to extend asymmetric bidirectional interface buses, such as Serial peripheral interface (SPI) over LVDS, to achieve long-distance and low-cost SPI communication.

The SN65LVDTxx is primarily used in point-to-point configurations, as seen in Figure 19. This configuration provides a clean signaling environment for the fast edge rates of the SN65LVDTxx and other LVDS components. The SN65LVDTxx should be connected through a balanced media, which could be a standard twisted pair cable, a parallel pair cable, or simply PCB traces to a LVDS receiver. Typically, the characteristic differential impedance of the media is in the range of 100 Ω . The SN65LVDTxx device is intended to drive a 100- Ω transmission line. The 100- Ω termination resistor is selected to match the media and is located as close to the LVDS receiver input pins as possible.

9.2 Functional Block Diagram

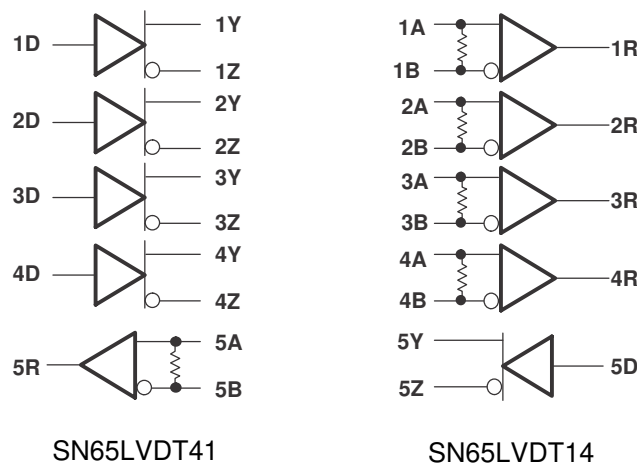


Figure 15. SN65LVDT41 (left) and SN65LVDT14 (Right) Functional Diagram

9.3 Feature Description

9.3.1 SN65LVDTxx Driver and Receiver Functionality

Table 2 shows how the LVDS receiver differential input to single-ended output relationship is defined for SN65LVDTxx. The SN65LVDTxx receiver is capable of detecting signals as low as 100 mV over a ± 1 -V common-mode range centered around 1.2 V.

Feature Description (continued)

Table 2. SN65LVDTxx Receiver Functionality

INPUTS	OUTPUT
$V_{ID} = V_A - V_B$	R
$V_{ID} \geq 100 \text{ mV}$	H
$-100 \text{ mV} < V_{ID} < 100 \text{ mV}$	?
$V_{ID} \leq -100 \text{ mV}$	L
Open	H

Table 3 shows how the LVDS driver single-ended input to differential output relationship is defined for SN65LVDTxx.

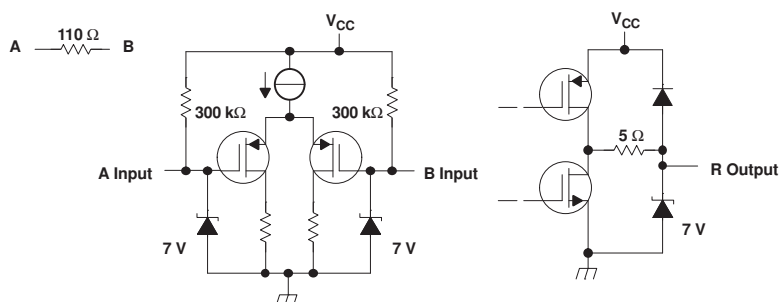
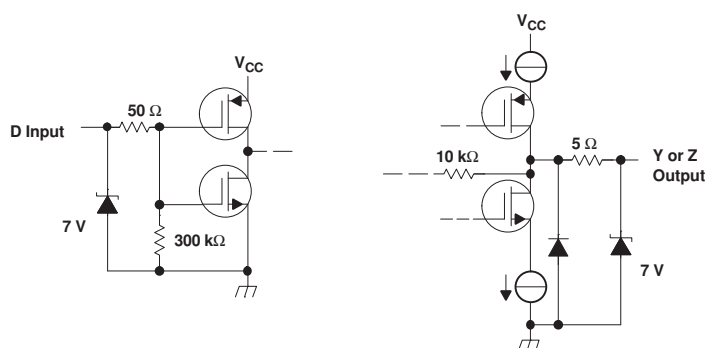
Table 3. SN65LVDTxx Receiver Functionality

INPUT	OUTPUTS	
D	Y	Z
H	H	L
L	L	H
Open	L	H

9.3.2 Integrated Termination

SN65LVDTxx integrates termination resistors for the LVDS receiver internal to the device. The resistor value will be between 88 Ω and 132 Ω . Additional termination resistors are not required on the receiver inputs of SN65LVDTxx.

9.3.3 SN65LVDTxx Equivalent Circuits


Figure 16. Receiver Equivalent Input and Output Schematic Diagrams

Figure 17. Driver Equivalent Input and Output Schematic Diagrams

9.4 Device Functional Modes

The device has one mode of operation that applies when operated within the *Recommended Operating Conditions*.

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The SN65LVDTxx devices are multi-channel LVDS driver and receiver pairs. The functionality of this device is simple yet extremely flexible, leading to its use in designs ranging from test and measurement to LED video wall. The varied class of potential applications share features and applications discussed in the paragraphs below.

10.1.1 Extending a Serial Peripheral Interface Using LVDS Signaling Over Differential Transmission Cables

Serial Peripheral Interface (SPI) is found in numerous applications as the communication method between processor and peripheral devices using single-ended signals over short distances. However, there is increasing demand for longer range SPI communication on the same PCB or from board to board. As distance increases, external noise, and electromagnetic interference (EMI) with single-ended SPI signals becomes an issue. Furthermore, increased distance limits the data rate due to propagation delay, and affects the signal quality due to potential ground shift between boards. A long distance SPI communication is achievable with the help of LVDS. LVDS, as specified by the TIA/EIA-644-A standard, provides several benefits when compared to alternative long-distance signaling technologies: low EMI, high noise immunity, low power consumption, and inexpensive interconnect cables.

SPI operates in a master-slave architecture, with four unidirectional signal lines. The master supplies data named Master-Out-Slave-In (MOSI), a clock (SCLK), and a optional Chip Select (CS) signal to control the operation of the system with multiple slave devices. The MOSI, SCLK, and $\overline{CS}$ signals are unidirectional from the master device to slave devices. The serial data from slave to master device is a unidirectional signal named Master-In-Slave-Out (MISO). The flow of data can be seen in [Figure 18](#).

SN65LVDT14 and SN65LVDT41 provide the necessary LVDS drivers and receivers specifically targeted at implementing a long distance SPI application. It uses the unidirectional links for the MOSI, MISO, SCLK, and CS signals and converts the single-ended data into a unidirectional LVDS links. SN65LVDT41 combines four LVDS line drivers with a single terminated LVDS line receiver in one package should be located at the SPI master device. SN65LVDT14 combines one LVDS line driver with four terminated LVDS line receivers in one package and should be located at the SPI device.

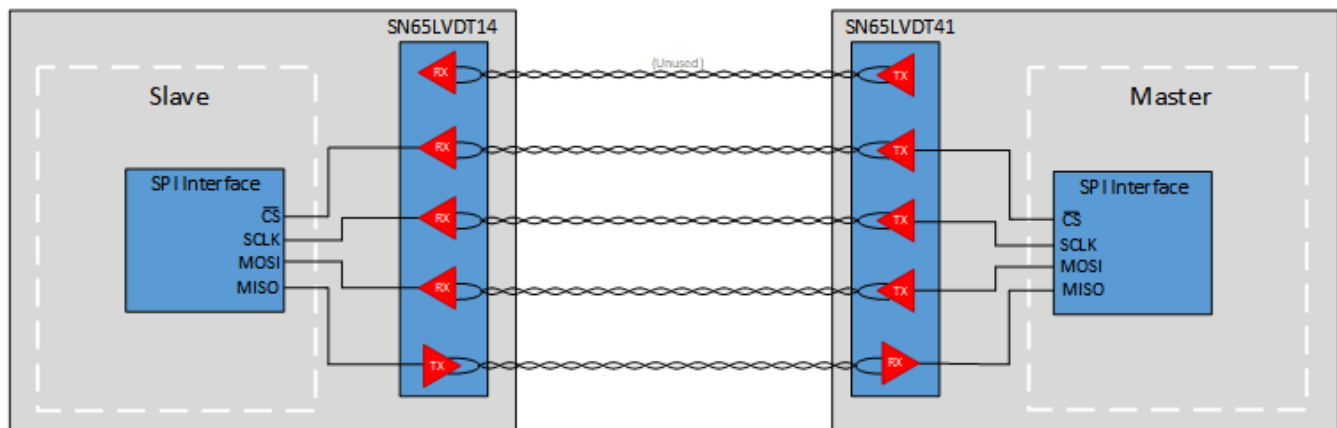


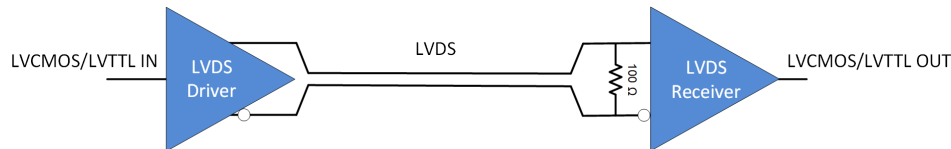
Figure 18. Typical SPI Application With LVDS

Table 4. SPI Design Parameters

Design Parameter	Example Value
Supply Voltage (V_{DD})	3 to 3.6 V
Single-ended Input Voltage	0 to V_{DD}
SPI Data Rate	0 to 10 Mbps
Interconnect Characteristic Impedance	100 Ω
Number of LVDS Channel	4
Number of Transmitter Nodes	3
Number of Receiver Nodes	1
Ground shift between driver and receiver	± 1 V

10.2 Typical Application

Point-to-Point applications provide a clean signaling environment for the fast edge rates of the SN65LVDTxx and other LVDS components. The SN65LVDTxx is connected through a balanced media which may be a standard twisted-pair cable, a parallel pair cable, or simply PCB traces to a LVDS receiver. Typically, the characteristic differential impedance of the media is in the range of 100 Ω . The SN65LVDTxx device is intended to drive a 100- Ω transmission line. The 100- Ω termination resistor is selected to match the media and is located as close to the LVDS receiver input pins as possible.


Figure 19. Typical LVDS Point-to-Point Application

10.2.1 Design Requirements

Table 5 lists the design parameters for typical point-to-point applications.

Table 5. Typical Design Parameters

Design Parameter	Example Value
Supply Voltage (V_{DD})	3 to 3.6 V
Single-ended Input Voltage	0 to V_{DD}
Data Rate	0 to 400 Mbps
Interconnect Characteristic Impedance	100 Ω
Number of LVDS Channel	5
Number of Receiver/Transmitter Nodes	5
Ground shift between driver and receiver	± 1 V

10.2.2 Detailed Design Procedure

10.2.2.1 SPI Propagation Delay Limitations

In typical SPI communication, the SPI master decides the sampling rate and data transfer rate, sends data at the rising edge of one clock cycle, and receives data on the falling edge within the same clock cycle. In a low latency system, the data in peripheral device should be made available to the host system with minimum delay. However in systems with high latency, the total round trip propagation delay of the SPI system must be less than half the SCLK period to avoid missing bits. There are three major delay contributors in a typical system—the SPI peripheral, data link device, and transmission media. Both the SPI peripheral and the data link device have fixed delay. The delay in transmission media, however, increases as communication distance increases. The relationship between cable length and SPI clock frequency can be seen in Figure 22. Figure 22 refers to a system where both MISO and MOSI are used, accounting for the case of slave-to-master data transmission, including roundtrip delay. The specific setup is described in [Extending SPI and McBSP with differential interface products](#) (SLLA142)

10.2.2.2 Interconnecting Media

The physical communication channel between the LVDS driver and the LVDS receiver may be any balanced and paired metal conductors meeting the requirements of the LVDS standard, the key points of which are included here. This media may be shielded twisted-pair cables, twinax cables, flat ribbon cables, or PCB traces. The nominal characteristic impedance of the interconnect media should be between 100 Ω and 120 Ω with a variation of no more than 10% (90 Ω to 132 Ω). Balanced cables (for example, twisted-pair) are usually better than unbalanced cables (like ribbon and simple coax cables) for noise reduction and signal quality. Balanced cables tend to generate less EMI due to field-canceling effects and also tend to pick up electromagnetic radiation a common-mode (not differential mode) noise which is rejected by the receiver. There should not introduce major impedance discontinuities in the system.

10.2.2.3 Input Fail-Safe Biasing

External pullup and pulldown resistors may be used to provide enough of an offset to enable an input fail-safe under open-circuit conditions. This configuration ties the positive LVDS input pin to VDD through a pullup resistor and the negative LVDS input pin is tied to GND by a pulldown resistor. The pullup and pulldown resistors should be in the 5-k Ω to 15-k Ω range to minimize loading and waveform distortion to the driver. The common-mode bias point should be set to approximately 1.2 V (less than 1.75 V) to be compatible with the internal circuitry. Refer to application note [AN-1194 Fail-safe biasing of LVDS interfaces](#) (SNLA051) for more information.

10.2.2.4 Power Decoupling Recommendations

Bypass capacitors must be used on power pins. Use high-frequency, ceramic (surface mount is recommended), 0.1- μ F and 0.001- μ F capacitors in parallel at the power supply pin with the smallest value capacitor closest to the device supply pin.

Bypass capacitors play a key role in power distribution circuitry. Specifically, they create low-impedance paths between power and ground. At low frequencies, a good digital power supply offers very low-impedance paths between its terminals. However, as higher frequency currents propagate through power traces, the source is quite often incapable of maintaining a low-impedance path to ground. Bypass capacitors are used to address this shortcoming. Usually, large bypass capacitors (10 μ F to 1000 μ F) at the board-level do a good job up into the kHz range. Due to their size and length of their leads, they tend to have large inductance values at the switching frequencies of modern digital circuitry. To solve this problem, one must resort to the use of smaller capacitors (nF to μ F range) installed locally next to the integrated circuit.

Multilayer ceramic chip or surface-mount capacitors (size 0603 or 0805) minimize lead inductances of bypass capacitors in high-speed environments, because their lead inductance is about 1 nH. For comparison purposes, a typical capacitor with leads has a lead inductance around 5 nH.

The value of the bypass capacitors used locally with LVDS chips can be determined by [Equation 1](#) and [Equation 2](#) according to Johnson⁽¹⁾ equations 8.18 to 8.21. A conservative rise time of 200 ps and a worst-case change in supply current of 1 A covers the whole range of LVDS devices offered by Texas Instruments. In this example, the maximum power supply noise tolerated is 200 mV. However, this figure varies depending on the noise budget available in the design. ⁽¹⁾

$$C_{\text{chip}} = \left(\frac{\Delta I_{\text{Maximum Step Change Supply Current}}}{\Delta V_{\text{Maximum Power Supply Noise}}} \right) \times T_{\text{Rise Time}} \quad (1)$$

$$C_{\text{LVDS}} = \left(\frac{1\text{A}}{0.2\text{V}} \right) \times 200\text{ ps} = 0.001\text{ }\mu\text{F} \quad (2)$$

[Figure 20](#) lowers lead inductance and covers intermediate frequencies between the board-level capacitor (>10 μ F) and the value of capacitance found above (0.001 μ F). TI recommends that the user place the smallest value of capacitance as close to the chip as possible.

(1) Howard Johnson & Martin Graham.1993. High Speed Digital Design – A Handbook of Black Magic. Prentice Hall PRT. ISBN number 013395724.

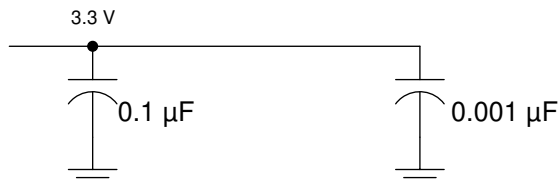


Figure 20. Recommended LVDS Bypass Capacitor Layout

10.2.2.5 PCB Transmission Lines

As per the [LVDS owner's manual design guide, 4th edition](#) (SNLA187), [Figure 21](#) depicts several transmission line structures commonly used in printed-circuit boards (PCBs). Each structure consists of a signal line and return path with a uniform cross section along its length. A microstrip is a signal trace on the top (or bottom) layer, separated by a dielectric layer from its return path in a ground or power plane. A stripline is a signal trace in the inner layer, with a dielectric layer in between a ground plane above and below the signal trace. The dimensions of the structure along with the dielectric material properties determine the characteristic impedance of the transmission line (also called controlled-impedance transmission line).

When two signal lines are placed close by, they form a pair of coupled transmission lines. [Figure 21](#) shows examples of edge-coupled microstrip lines, and edge-coupled or broad-side-coupled striplines. When excited by differential signals, the coupled transmission line is referred to as a differential pair. The characteristic impedance of each line is called odd-mode impedance. The sum of the odd-mode impedances of each line is the differential impedance of the differential pair. In addition to the trace dimensions and dielectric material properties, the spacing between the two traces determines the mutual coupling and impacts the differential impedance. When the two lines are immediately adjacent (like if S is less than $2W$, for example), the differential pair is called a tightly-coupled differential pair. To maintain constant differential impedance along the length, it is important to keep the trace width and spacing uniform along the length, as well as maintain good symmetry between the two lines.

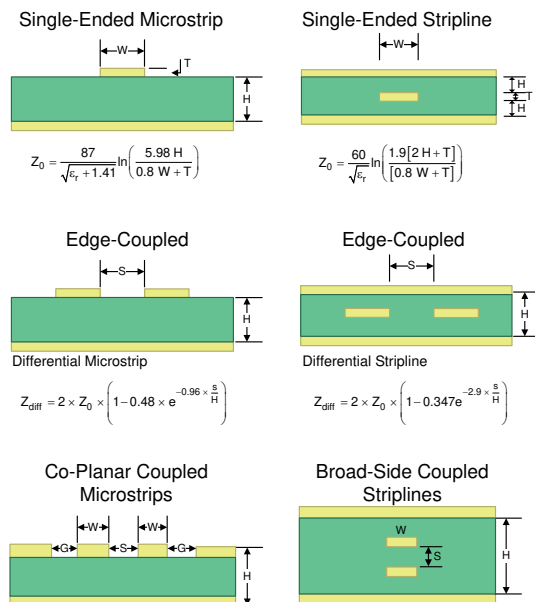


Figure 21. Controlled-Impedance Transmission Lines

10.2.2.6 Probing LVDS Transmission Lines on PCB

Always use high impedance ($> 100 \text{ k}\Omega$), low capacitance ($< 2 \text{ pF}$) scope probes with a wide bandwidth (1 GHz) scope. Improper probing will skew results.

10.2.3 Application Curve

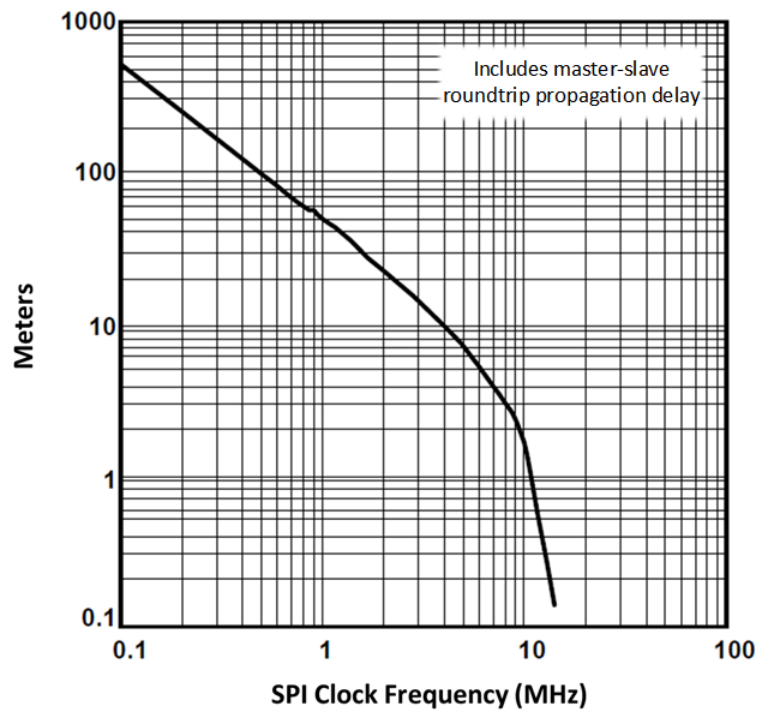


Figure 22. SN65LVDTxx SPI Performance: Cable Length vs SPI Clock

11 Power Supply Recommendations

The SN65LVDTxx devices are designed to operate from a single power supply with a supply voltage range of 3 V to 3.6 V. In a typical point-to-point application, a driver and a receiver may be on separate boards, or even separate equipment. In these cases, separate supplies would be used at each location. The expected ground potential difference between the driver power supply and the driver power supply would be less than $|\pm 1 \text{ V}|$. Board level and local device level bypass capacitance should be used.

12 Layout

12.1 Layout Guidelines

12.1.1 Microstrip vs. Stripline Topologies

As per the [LVDS application and data handbook](#) (SLLD009), printed-circuit boards usually offer designers two transmission line options: microstrip and stripline. Microstrips are traces on the outer layer of a PCB, as shown in [Figure 23](#).

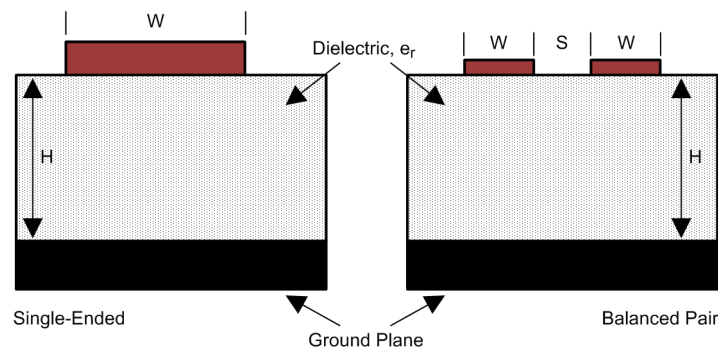


Figure 23. Microstrip Topology

On the other hand, striplines are traces between two ground planes. Striplines are less prone to emissions and susceptibility problems because the reference planes effectively shield the embedded traces. However, from the standpoint of high-speed transmission, juxtaposing two planes creates additional capacitance. TI recommends routing LVDS signals on microstrip transmission lines when possible. The PCB traces allow designers to specify the necessary tolerances for Z_0 based on the overall noise budget and reflection allowances. Footnotes 1⁽²⁾, 2⁽³⁾, and 3⁽⁴⁾ provide formulas for Z_0 and t_{PD} for differential and single-ended traces. ⁽²⁾ ⁽³⁾ ⁽⁴⁾

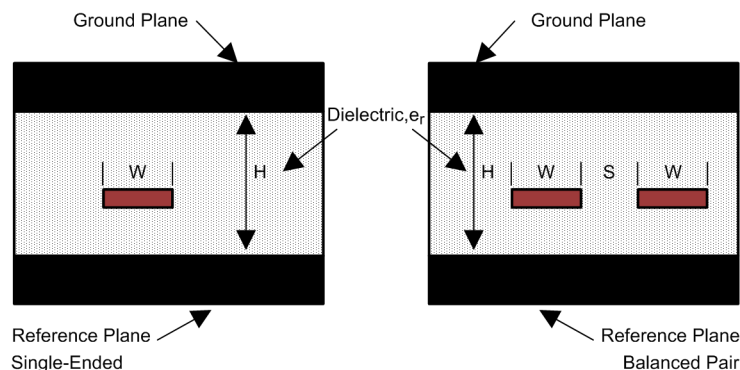


Figure 24. Stripline Topology

(2) Howard Johnson & Martin Graham. 1993. High Speed Digital Design – A Handbook of Black Magic. Prentice Hall PRT. ISBN number 013395724.

(3) Mark I. Montrose. 1996. Printed Circuit Board Design Techniques for EMC Compliance. IEEE Press. ISBN number 0780311310.

(4) Clyde F. Coombs, Jr. Ed, Printed Circuits Handbook, McGraw Hill, ISBN number 0070127549.

Layout Guidelines (continued)

12.1.2 Dielectric Type and Board Construction

The speeds at which signals travel across the board dictates the choice of dielectric. FR-4, or an equivalent, usually provides adequate performance for use with LVDS signals. If rise or fall times of LVCMOS/LVTTL signals are less than 500 ps, empirical results indicate that a material with a dielectric constant near 3.4, such as Rogers™ 4350 or Nelco N4000-13, may be desired. Once the designer chooses the dielectric, there are several parameters pertaining to the board construction that can affect performance. The following set of guidelines were developed experimentally through several designs involving LVDS devices:

- Copper weight: 15 g or 1/2 oz start, plated to 30 g or 1 oz
- All exposed circuitry should be solder-plated (60/40) to 7.62 μm or 0.0003 in (minimum).
- Copper plating should be 25.4 μm or 0.001 in (minimum) in plated-through-holes.
- Solder mask over bare copper with solder hot-air leveling

12.1.3 Recommended Stack Layout

Following the choice of dielectrics and design specifications, the designer must decide how many levels to use in the stack. To reduce the LVCMOS/LVTTL to LVDS crosstalk, it is good practice to have at least two separate signal planes as shown in [Figure 25](#).

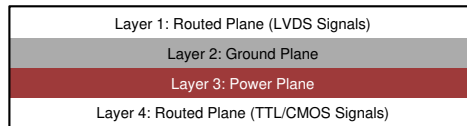


Figure 25. Four-Layer PCB Board

NOTE

The separation between layers 2 and 3 should be 127 μm (0.005 in). By keeping the power and ground planes tightly coupled, the increased capacitance acts as a bypass for transients.

One of the most common stack configurations is the six-layer board, as shown in [Figure 26](#).

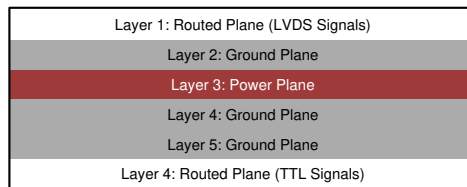


Figure 26. Six-Layer PCB Board

In this particular configuration, it is possible to isolate each signal layer from the power plane by at least one ground plane. The result is improved signal integrity, but fabrication is more expensive. Using the 6-layer board is preferable, because it offers the layout designer more flexibility in varying the distance between signal layers and referenced planes in addition to ensuring reference to a ground plane for signal layers 1 and 6.

12.1.4 Separation Between Traces

The separation between traces depends on several factors, but the amount of coupling that can be tolerated usually dictates the actual separation. Low-noise coupling requires close coupling between the differential pair of an LVDS link to benefit from the electromagnetic field cancellation. The traces should be 100- Ω differential and thus coupled in the manner that best fits this requirement. In addition, differential pairs should have the same electrical length to ensure that they are balanced, thus minimizing problems with skew and signal reflection.

Layout Guidelines (continued)

In the case of two adjacent single-ended traces, one should use the 3-W rule, which stipulates that the distance between two traces must be greater than two times the width of a single trace, or three times its width measured from trace center to trace center. This increased separation effectively reduces the potential for crosstalk. The same rule should be applied to the separation between adjacent LVDS differential pairs, whether the traces are edge-coupled or broad-side-coupled.

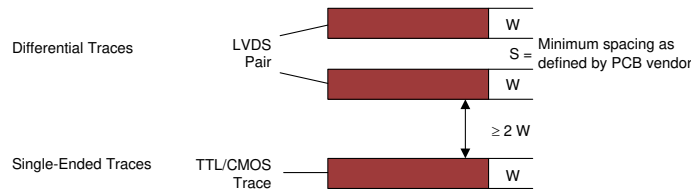


Figure 27. 3-W Rule for Single-Ended and Differential Traces (Top View)

Exercise caution when using autorouters, because they do not always account for all factors affecting crosstalk and signal reflection. For instance, it is best to avoid sharp 90° turns to prevent discontinuities in the signal path. Using successive 45° turns tends to minimize reflections.

12.1.5 Crosstalk and Ground Bounce Minimization

To reduce crosstalk, it is important to provide a return path to high-frequency currents that is as close to its originating trace as possible. A ground plane usually achieves this. Because the returning currents always choose the path of lowest inductance, they are most likely to return directly under the original trace, thus minimizing crosstalk. Lowering the area of the current loop lowers the potential for crosstalk. Traces kept as short as possible with an uninterrupted ground plane running beneath them emit the minimum amount of electromagnetic field strength. Discontinuities in the ground plane increase the return path inductance and should be avoided.

12.1.6 Decoupling

Each power or ground lead of a high-speed device should be connected to the PCB through a low inductance path. For best results, one or more vias are used to connect a power or ground pin to the nearby plane. TI recommends that the user place a via immediately adjacent to the pin to avoid adding trace inductance. Placing a power plane closer to the top of the board reduces the effective via length and its associated inductance.

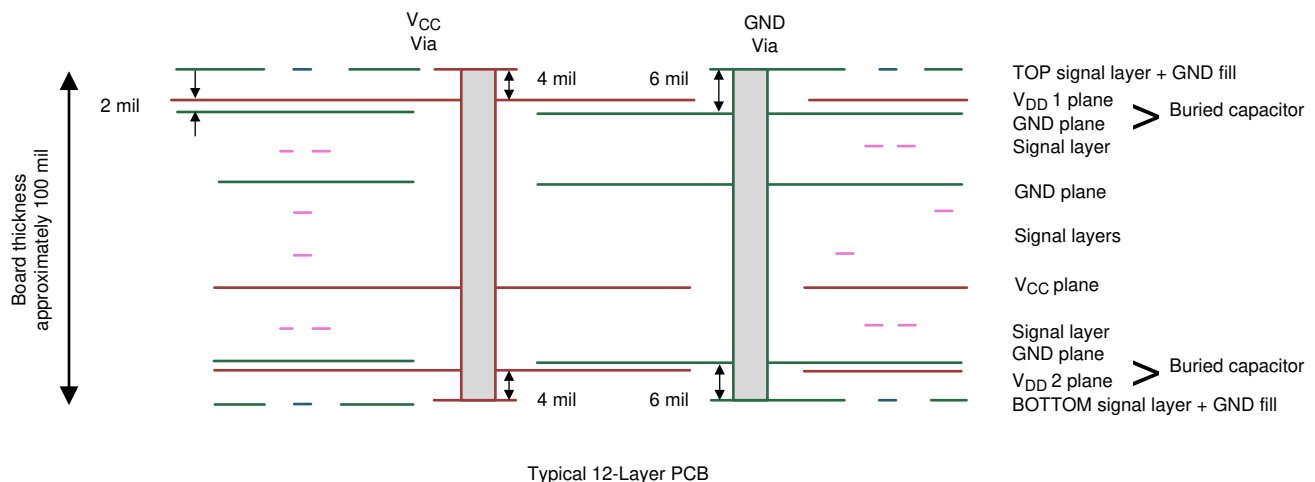


Figure 28. Low Inductance, High-Capacitance Power Connection

Layout Guidelines (continued)

Bypass capacitors should be placed close to V_{DD} pins. They can be placed conveniently near the corners or underneath the package to minimize the loop area. This extends the useful frequency range of the added capacitance. Small-physical-size capacitors, such as 0402 or even 0201, or X7R surface-mount capacitors should be used to minimize body inductance of capacitors. Each bypass capacitor is connected to the power and ground plane through vias tangent to the pads of the capacitor as shown in Figure 29(a).

An X7R surface-mount capacitor of size 0402 has about 0.5 nH of body inductance. At frequencies above 30 MHz or so, X7R capacitors behave as low-impedance inductors. To extend the operating frequency range to a few hundred MHz, an array of different capacitor values like 100 pF, 1 nF, 0.03 μ F, and 0.1 μ F are commonly used in parallel. The most effective bypass capacitor can be built using sandwiched layers of power and ground at a separation of 2 to 3 mils. With a 2-mil FR4 dielectric, there is approximately 500 pF per square inch of PCB. Refer back to Figure 21 for some examples. Many high-speed devices provide a low-inductance GND connection on the backside of the package. This center dap must be connected to a ground plane through an array of vias. The via array reduces the effective inductance to ground and enhances the thermal performance of the small Surface Mount Technology (SMT) package. Placing vias around the perimeter of the dap connection ensures proper heat spreading and the lowest possible die temperature. Placing high-performance devices on opposing sides of the PCB using two GND planes (as shown in Figure 21) creates multiple paths for heat transfer. Often thermal PCB issues are the result of one device adding heat to another, resulting in a very high local temperature. Multiple paths for heat transfer minimize this possibility. In many cases the GND dap that is so important for heat dissipation makes the optimal decoupling layout impossible to achieve due to insufficient pad-to-dap spacing as shown in Figure 29(b). When this occurs, placing the decoupling capacitor on the backside of the board keeps the extra inductance to a minimum. It is important to place the V_{DD} via as close to the device pin as possible while still allowing for sufficient solder mask coverage. If the via is left open, solder may flow from the pad and into the via barrel. This will result in a poor solder connection.



Figure 29. Typical Decoupling Capacitor Layouts

At least two or three times the width of an individual trace should separate single-ended traces and differential pairs to minimize the potential for crosstalk. Single-ended traces that run in parallel for less than the wavelength of the rise or fall times usually have negligible crosstalk. Increase the spacing between signal paths for long parallel runs to reduce crosstalk. Boards with limited real estate can benefit from the staggered trace layout, as shown in Figure 30.

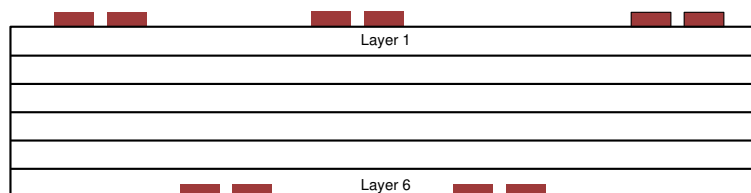


Figure 30. Staggered Trace Layout

This configuration lays out alternating signal traces on different layers. Thus, the horizontal separation between traces can be less than 2 or 3 times the width of individual traces. To ensure continuity in the ground signal path, TI recommends having an adjacent ground via for every signal via, as shown in Figure 31. Note that vias create additional capacitance. For example, a typical via has a lumped capacitance effect of 1/2 pF to 1 pF in FR4.

Layout Guidelines (continued)

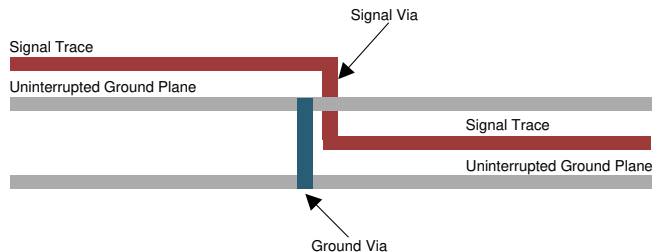


Figure 31. Ground Via Location (Side View)

Short and low-impedance connection of the device ground pins to the PCB ground plane reduces ground bounce. Holes and cutouts in the ground planes can adversely affect current return paths if they create discontinuities that increase returning current loop areas.

To minimize EMI problems, TI recommends avoiding discontinuities below a trace (for example, holes, slits, and so on) and keeping traces as short as possible. Zoning the board wisely by placing all similar functions in the same area, as opposed to mixing them together, helps reduce susceptibility issues.

12.2 Layout Examples

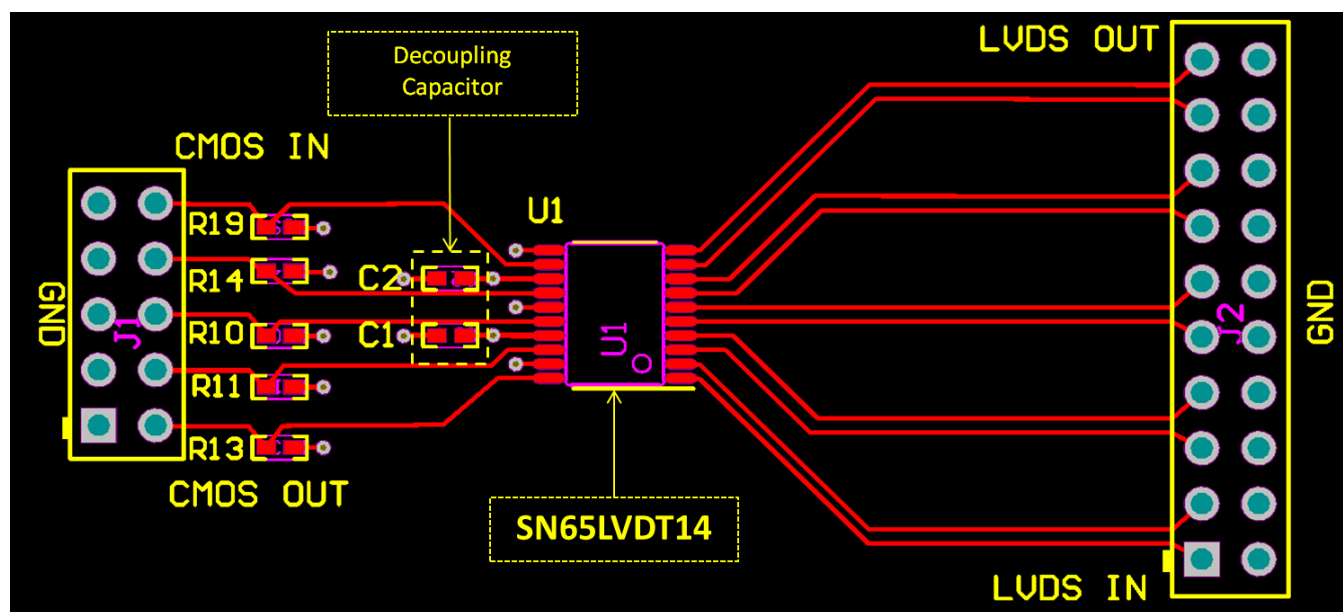


Figure 32. Example SN65LVDT14 Layout

SN65LVDT14, SN65LVDT41

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Layout Examples (continued)

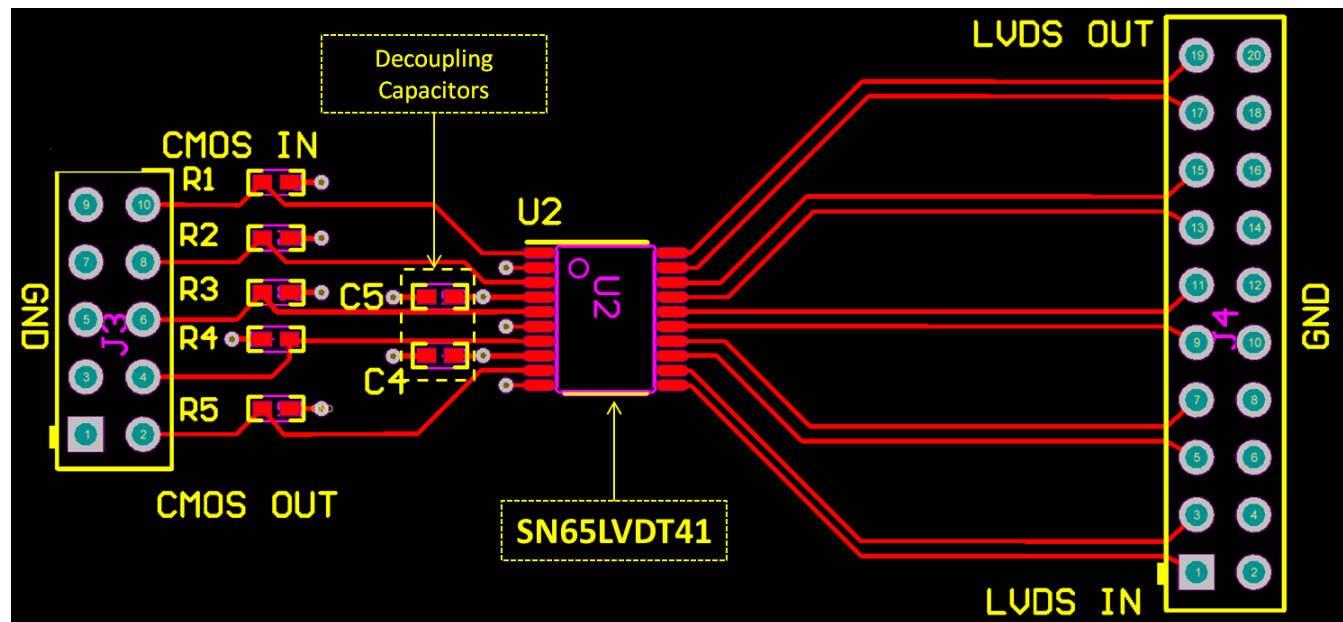


Figure 33. Example SN65LVDT41

13 デバイスおよびドキュメントのサポート

13.1 関連資料

関連資料については、以下を参照してください。

- 『LVDSオーナー・マニュアル』(SNLA187)
- 『AN-808、長い伝送ラインとデータ信号の品質』(SNLA028)
- 『AN-977、LVDS信号の品質: アイ・パターンを使用したジッタ測定のテスト・レポート #1』(SNLA166)
- 『AN-971、LVDSテクノロジーの概要』(SNLA165)
- 『AN-916、ケーブル選択の実践的ガイド』(SNLA219)
- 『AN-805、差動ライン・ドライバの消費電力の計算』(SNOA233)
- 『AN-903、差動終端技法の比較』(SNLA034)
- 『AN-1194、LVDSインターフェイスのフェイルセーフ・バイアス法』(SNLA051)

13.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

13.3 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびご注文へのクイック・アクセスが含まれます。

表 6. 関連リンク

製品	プロダクト・フォルダ	ご注文はこちら	技術資料	ツールとソフトウェア	サポートとコミュニティ
SN65LVDT14	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック
SN65LVDT41	ここをクリック	ここをクリック	ここをクリック	ここをクリック	ここをクリック

13.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.5 商標

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Serial Peripheral Interface is a trademark of Motorola.
Rogers is a trademark of Rogers Corporation.
All other trademarks are the property of their respective owners.

13.6 静電気放電に関する注意事項



すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

13.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN65LVDT14PW	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT14
SN65LVDT14PW.B	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT14
SN65LVDT14PWG4	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT14
SN65LVDT14PWR	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT14
SN65LVDT14PWR.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT14
SN65LVDT41PW	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41
SN65LVDT41PW.B	Active	Production	TSSOP (PW) 20	70 TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41
SN65LVDT41PWR	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41
SN65LVDT41PWR.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41
SN65LVDT41PWR1G4	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41
SN65LVDT41PWR1G4.B	Active	Production	TSSOP (PW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LVDT41

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF SN65LVDT14, SN65LVDT41 :

- Enhanced Product : [SN65LVDT14-EP](#), [SN65LVDT41-EP](#)

NOTE: Qualified Version Definitions:

- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65LVDT14PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN65LVDT41PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1
SN65LVDT41PWR1G4	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

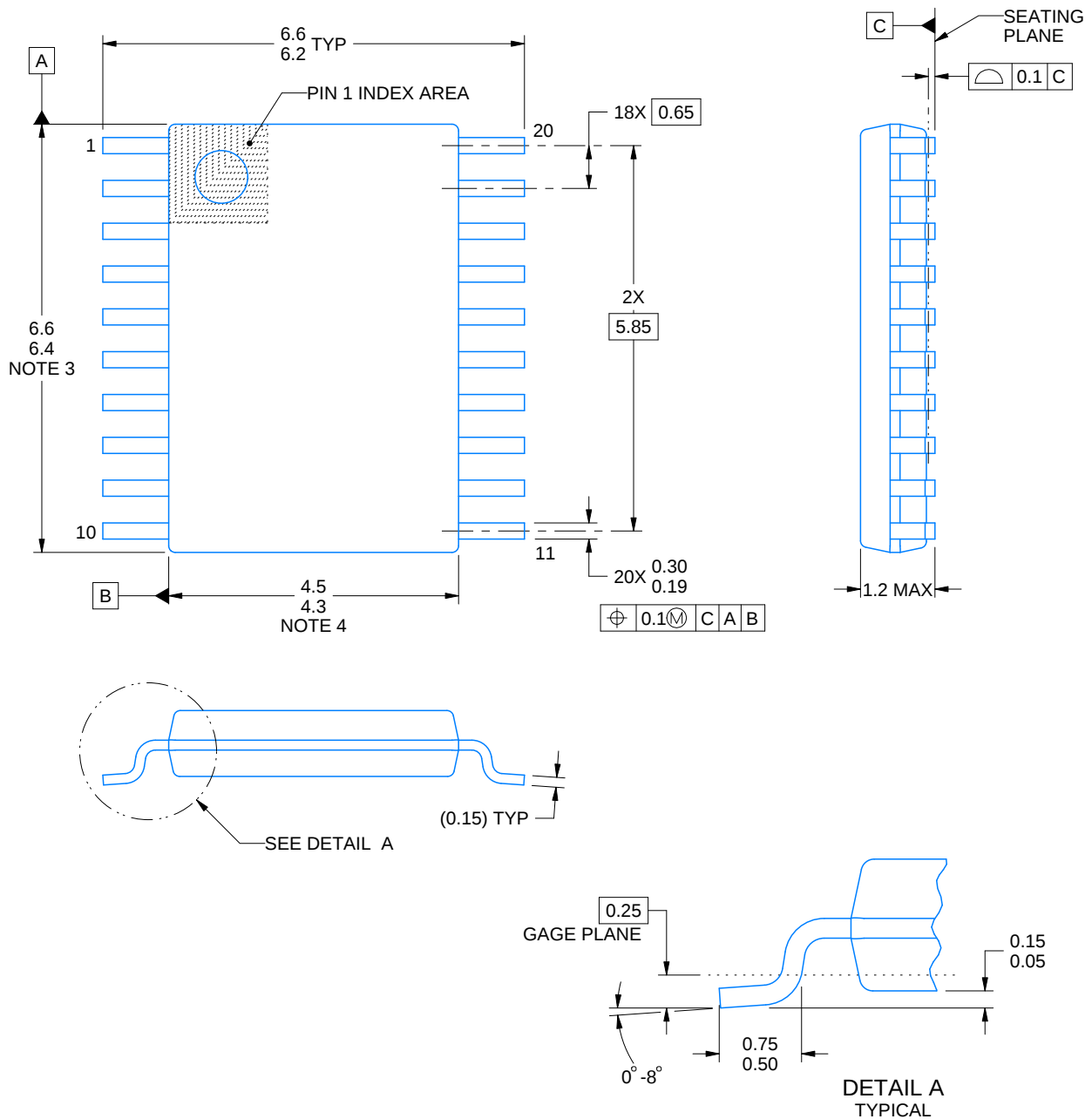
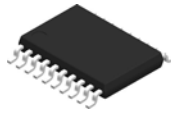
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65LVDT14PWR	TSSOP	PW	20	2000	353.0	353.0	32.0
SN65LVDT41PWR	TSSOP	PW	20	2000	353.0	353.0	32.0
SN65LVDT41PWR1G4	TSSOP	PW	20	2000	353.0	353.0	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65LVDT14PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT14PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT14PW.B	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT14PW.B	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT14PWG4	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT14PWG4	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT41PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT41PW	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT41PW.B	PW	TSSOP	20	70	530	10.2	3600	3.5
SN65LVDT41PW.B	PW	TSSOP	20	70	530	10.2	3600	3.5



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NOTES:

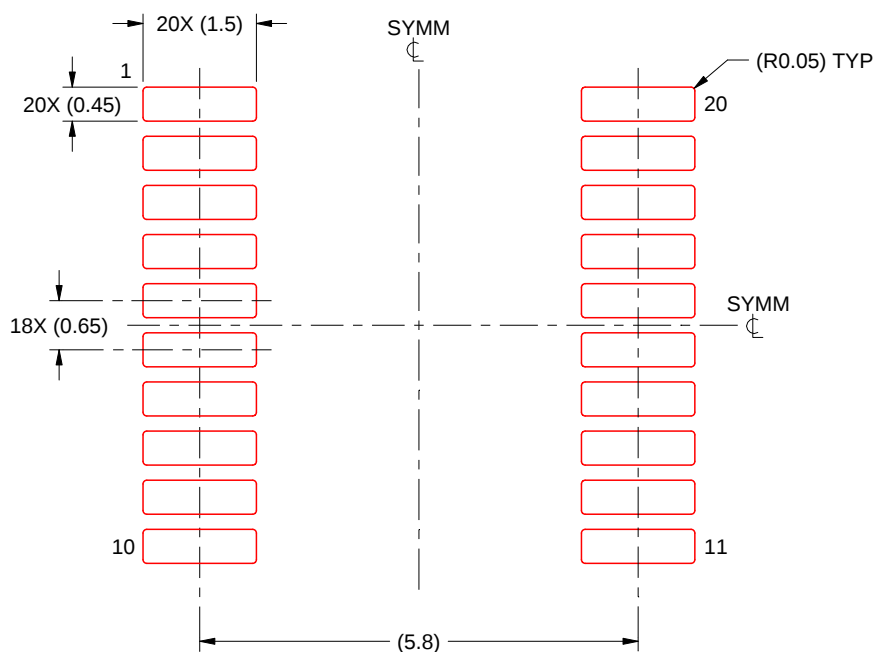
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE STENCIL DESIGN

PW0020A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

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最終更新日：2025 年 10 月